

## **BCX79**



# **PNP General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 68. See PN200A for characteristics.

### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	45	V
V <sub>CES</sub>	Collector-Base Voltage	45	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	500	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		BCX79	
P <sub>D</sub>	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

# PNP General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
	DACTEDICTICS				
	RACTERISTICS	1		T	T
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	45		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 1.0 \mu\text{A},  I_C = 0$	5.0		V
I <sub>CEX</sub>	Collector Cutoff Current	$V_{CE} = 45 \text{ V}, V_{BE} = 0.2 \text{ V},$ $T_A = +100 ^{\circ}\text{C}$		20	μΑ
I <sub>CES</sub>	Collector Cutoff Current	$V_{CE} = 45 \text{ V}, I_{E} = 0,$		10	nA
1	Emitter Cutoff Current	$V_{CE} = 45 \text{ V}, I_E = 0, T_A = +125 \text{ °C}$ $V_{EB} = 4.0 \text{ V}, I_C = 0$		2.5	μA
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$		20	nA
ON CHAR	ACTERISTICS DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 2.0 \text{ mA}$ $V_{CF} = 1.0 \text{ V}, I_{C} = 10 \text{ mA}$	120 80	630 1,000	
		$V_{CE} = 1.0 \text{ V}, I_{C} = 100 \text{ mA}$	40	,	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 2.5 \text{ mA}$		0.6	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 2.5 \text{ mA}$		1.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 2.0 \text{ mA}$	0.6	0.7	V
		$V_{CE} = 1.0 \text{ V}, I_{C} = 100 \text{ mA}$		0.9	V
SMALL S	IGNAL CHARACTERISTICS  Collector-Base Capacitance	V <sub>CB</sub> = 10 V, f = 1.0 MHz		4.5	pF
C <sub>eb</sub>	Emitter-Base Capacitance	V <sub>EB</sub> = 0.5 V, f = 1.0 MHz		15	pF
h <sub>ie</sub>	Input Impedance	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 1.0  kHz	1.6	8.5	kΩ
···le		1 1 - 1.0 N 12			
	Output Admittance	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 1.0  kHz		100	μmhos
h <sub>oe</sub>	Output Admittance  Noise Figure	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$		100 6.0	μmhos dB
h <sub>oe</sub> NF SWITCHI	Noise Figure  NG CHARACTERISTICS	$\begin{split} I_C &= 2.0 \text{ mA}, \ V_{CE} = 5.0 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ V_{CE} &= 5.0 \text{ V}, \ I_C = 0.2 \text{ mA}, \\ R_S &= 2.0 \text{ k}\Omega, \ \ f = 1.0 \text{ kHz} \end{split}$		6.0	
NF SWITCHI	Noise Figure  NG CHARACTERISTICS  Turn-on Time	$\begin{split} I_C &= 2.0 \text{ mA}, \ V_{CE} = 5.0 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ V_{CE} &= 5.0 \text{ V}, \ I_C = 0.2 \text{ mA}, \\ R_S &= 2.0 \text{ k}\Omega, \ f = 1.0 \text{ kHz} \\ \end{split}$ $V_{CC} &= 10 \text{ V}, \ I_C = 10 \text{ mA}, \\ V_{BB} &= 3.6 \text{ V}, \ I_{B1} = I_{B2} = 1.0 \text{ mA} \end{split}$		6.0	dB
NF SWITCHI	Noise Figure  NG CHARACTERISTICS  Turn-on Time  Turn-on Time	$\begin{split} I_C &= 2.0 \text{ mA}, \ V_{CE} = 5.0 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ V_{CE} &= 5.0 \text{ V}, \ I_C = 0.2 \text{ mA}, \\ R_S &= 2.0 \text{ k}\Omega, \ f = 1.0 \text{ kHz} \\ \end{split}$ $V_{CC} &= 10 \text{ V}, \ I_C = 10 \text{ mA}, \\ V_{BB} &= 3.6 \text{ V}, \ I_{B1} = I_{B2} = 1.0 \text{ mA} \\ V_{CC} &= 10 \text{ V}, \ I_C = 100 \text{ mA}, \\ V_{BB} &= 5.0 \text{ V}, \ I_{B1} = I_{B2} = 10 \text{ mA} \end{split}$		6.0 150 150	dB
NF SWITCHI	Noise Figure  NG CHARACTERISTICS  Turn-on Time	$\begin{split} I_C &= 2.0 \text{ mA}, \ V_{CE} = 5.0 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ V_{CE} &= 5.0 \text{ V}, \ I_C = 0.2 \text{ mA}, \\ R_S &= 2.0 \text{ k}\Omega, \ f = 1.0 \text{ kHz} \\ \end{split}$ $V_{CC} &= 10 \text{ V}, \ I_C = 10 \text{ mA}, \\ V_{BB} &= 3.6 \text{ V}, \ I_{B1} = I_{B2} = 1.0 \text{ mA}, \\ V_{CC} &= 10 \text{ V}, \ I_C = 100 \text{ mA}, \\ \end{split}$		6.0	dB

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